

APPLICATION: Low Frequency Power Amplifier Application.

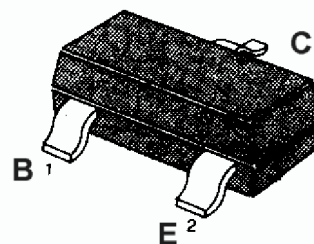
—PNP silicon—

Power Switching Applications.

**MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	-35	V
Collector-emitter voltage	V <sub>CE0</sub>	-30	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-1500	mA
Collector Power Dissipation	P <sub>C</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C

**SOT-23**



1.Base 2.Emitter 3.Collector

**ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	100		320		V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA
Collector Cut-off Current	I <sub>CB0</sub>			-0.1	μA	V <sub>CB</sub> = -30V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			-0.1	μA	V <sub>EB</sub> = -5V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	-35			V	I <sub>C</sub> = -1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CE0</sub>	-30			V	I <sub>C</sub> = -10mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -1mA, I <sub>C</sub> =0
Base-Emitter Voltage	V <sub>BE</sub>	-0.5		-0.8	V	V <sub>CE</sub> = -1V, I <sub>C</sub> = -10mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			-0.4	V	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Gain bandwidth product	f <sub>T</sub>	100	120		MHz	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5V
Common Base Output Capacitance	C <sub>ob</sub>		13		PF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz

**h<sub>FE</sub> Classification And Marking**

Print Mark

IY

h<sub>FE</sub>

160~320

